

SEMICONDUCTOR DEVICE SUBSTRATE

ABSTRACT OF THE DISCLOSURE

A semiconductor device substrate comprised of a core substrate on both surfaces or on one surface of which interconnect patterns are formed via resin layers, wherein the core substrate is formed by a material having a heat expansion coefficient close to a semiconductor chip, that is, a heat expansion coefficient closer to a semiconductor chip than the resin layers and the interconnect patterns inside the substrate, a resin layer forming an outermost layer of the substrate is formed using a material having a higher strength and/or a higher elongation than the resin material used for the inner resin layers in the substrate, and thereby cracking, deformation, and other problems arising in the substrate due to the thermal stress occurring between the core substrate and the resin layers in the substrate and interconnect patterns being prevented.